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High performance perovskite solar cells using Cu$_9$S$_5$ supraparticles incorporated hole transport layers

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Abstract

We disclose novel photovoltaic device physics and present details of device mechanisms by investigating perovskite solar cells (PSCs) incorporating Cu$_9$S$_5$@SiO$_2$ supraparticles (SUPs) into Spiro-OMeTAD based hole transport layers (HTLs). High quality colloidal Cu$_9$S$_5$ nanocrystals (NCs) were prepared using a hot-injection approach. Multiple Cu$_9$S$_5$ NCs were further embedded in silica to construct a Cu$_9$S$_5$@SiO$_2$ SUP. Cu$_9$S$_5$@SiO$_2$ SUPs were blended into Spiro-OMeTAD based HTLs with different weight ratios. Theoretical and experimental results show that the very strong light scattering or reflecting properties of Cu$_9$S$_5$@SiO$_2$ SUPs blended in the PSC device in a proper proportion distribute to increase the light energy trapped within the device, leading to significant enhancement of light absorption in the active layer. Additionally, the incorporated Cu$_9$S$_5$@SiO$_2$ SUPs can also promote the electrical conductivity and hole-transport capacity of the HTL. Significantly larger conductivity and higher hole injection efficiency were demonstrated in the HTM with the optimal weight ratios of Cu$_9$S$_5$@SiO$_2$ SUPs. As a result, efficient Cu$_9$S$_5$ SUPs based PSC devices were obtained with average power conversion efficiency (PCE) of 18.21% at an optimal weight ratio of Cu$_9$S$_5$ SUPs. Compared with PSC solar cells without Cu$_9$S$_5$@SiO$_2$ SUPs (of which the average PCE is 14.38%), a remarkable enhancement over 26% in average PCE was achieved. This study provides an innovative approach to efficiently promote the performance of PSC devices by employing optically stable, low-cost and green p-type semiconductor SUPs.

Supplementary material for this article is available online

(Some figures may appear in colour only in the online journal)

1. Introduction

Perovskite solar cells (PSCs) based on organometal halides have recently emerged as a prominent, efficient and low-cost solar technology. PSC devices originate from a liquid-based dye sensitized solar cells (DSSCs). In this liquid-based DSSC structure, the adsorption of CH$_3$NH$_3$PbI$_3$ perovskite on a porous nanocrystalline TiO$_2$ electrode generates a photocurrent and gains a power conversion efficiency (PCE) of about 3%–4%, as first reported in 2009 [1]. However, the

stability issues of the liquid-based PSC cell are very severe, including immediate disintegration of the perovskite sensitizer in a liquid electrolyte. Stable PSCs with a PCE of about 10% were developed by substituting the liquid electrolyte with a solid hole conductor in 2012 [2–4]. Then, solid-state PSCs have attracted a great deal of attention. Efficiencies have quickly risen from 3.8% [1] to 23.7% [5] in just nine years. Generally, PSCs comprise multiple functional layers and interfaces [3, 6–9]. Comprehending the function and mechanisms of the components in PSC devices can expedite advancements in PSC efficiency and stability [10]. Presently, a lot of academic scientists and researchers are concentrated on promoting the quality of the perovskite active layer and electron transport layer (ETL) using anti-solvent, additive or other novel procedures [11], and mastering their working mechanisms [12]. However, researches into the function of additives in the hole transport layer (HTL) are quite limited [13, 14].

One of the most important advancements for PSC devices in the past several years is the replacement of the liquid electrolyte with the solid-state hole transporting material (HTM) 2,2′,7,7′-tetrakis(*N*,*N*-di-*p*-methoxyphenylamine)-9,9′-spirobifluorene (Spiro-OMeTAD). This substitution dramatically improves the stability and the efficiency of PSCs [3, 15]. In spite of the benefits that it brings to PSCs, the pristine uncharged form of Spiro-OMeTAD suffers from intrinsic low hole mobility and low conductivity. Effective strategies are needed to solve the inherent shortages, such as adding dopants. Actually, Spiro-OMeTAD is the generally used HTM in solid-state dye sensitized solar cells (SDSSCs). During the development of the SDSSC technology, chemical p-dopants like $N(PhBr)_3SbCl_6$ were introduced to oxidize and dope Spiro-OMeTAD for the first time. Shortly afterwards, it were substituted with bis(trifluoromethane)sulfonimide lithium salt (LiTFSI) and 4-tert-butylpyridine (tBP) [16–18]. LiTFSI is the p-dopant, and tBP is the additive that acts as a recombination blocking agent. This combination was initially employed to SDSSCs, and extensively utilized to PSCs to date [19]. In addition, Cobalt dopants and perfluoro-tetracyanoquinodimethane F_4TCNQ have also been exploited to enhance the hole conductivity of Spiro-OMeTAD [20, 21]. Therefore, additives play an important part in promoting the hole conductivity of the Spiro-OMeTAD film and eventually raise the efficiency of PSCs.

Copper sulfides with a formula of $Cu_{2-x}S$ ($0 \leqslant x < 1$) have been widely investigated as plasmonic semiconductors. They are intrinsic hole-conducting (p-type) and direct band semiconductors, and their bandgap is in the range of 1.2–2.5 eV, depending on the specific phase and stoichiometry. $Cu_{2-x}S$ is a low-cost, environmentally benign and nontoxic material [22, 23]. Moreover, the nonstoichiometric copper sulfide nanocrystals (NCs) display near-infrared (NIR) localized surface plasmonic resonance (LSPR) absorption from excessive holes in the valence band due to the presence of copper vacancies, which endows them with the ability to fundamentally tailor light–matter interactions and potential applications in bio-imaging [24], photothermal therapy [25] and optical devices [26]. Zhang *et al* reported a molecular

precursor solution method to prepare Cu_9S_5 thin film as the back electrode of a CdTe solar cell [27]. Lei *et al* assembled PSCs based on a doped Spiro-OMeTAD/$Cu_{7.5}$S double layered HTM by vacuum thermal evaporation of CuS powders, reaching a PCE of 17.91% [28]. Very recently, Han *et al* fabricated a planar PSC with an undoped Spiro-OMeTAD/Cu_9S_5 double layered HTM and nitrogen doped SnO_2 ETL, achieving a maximum PCE of 17.10% [29]. Cu_9S_5 was proven to be a superior HTL and electrode interface modification layer in both polymer and PSC solar cells [29, 30]. It shows a splendid electrical conductivity, high mobility of copper ions, high work function and a suitable energy level alignment with the perovskite absorber. Copper chalcogenide nanomaterials are still in their initial PSC application stages, which have a humongous measure of space for further advancement. The efficiency of the PSCs can be promoted by the insertion of Cu_9S_5, an inorganic material, to construct a high quality organic and inorganic hybrid HTL. Additionally, as well known, the light–matter interaction in noble metal (gold and silver) nanostructures has extensively studied in order to improve photon absorption and thus improve the photon-to-electron conversion efficiency of photovoltaic (PV) devices [31]. Through rational designs, surface plasmon resonance of plasmonic semiconductor nanostructures could also help to enhance the solar energy harvesting by different mechanisms involving plasmon-enhanced solar light harvesting, hot carrier injection, resonant energy transfer, near-field enhancement and scattering (far -field effect) [32–35]. Cu_9S_5 NCs in a suitable configuration hybridized with organic HTM can be expected to optically engineer the PSC device to maximize light coupling/trapping into the photoactive layer due to their unique optical natures, including LSPR and scattering effects in the NIR range as well as low dissipation in the visible wavelength [36].

In this work, for the first time to our knowledge, $Cu_9S_5@SiO_2$ supraparticles (SUPs) are employed in HTLs to improve the PV performance of PSCs. High quality colloidal Cu_9S_5 nanocrystals (NCs) were synthesized via a hot-injection method. Multiple Cu_9S_5 NCs were further embedded in silica to form a $Cu_9S_5@SiO_2$ SUP. The synthesized $Cu_9S_5@SiO_2$ SUPs were incorporated in Spiro-OMeTAD based HTLs with different weight ratios. The weight ratio of $Cu_9S_5@SiO_2$ UPs has a great impact on the PV performance of the PSC device. It was found that with the addition of the Cu_9S_5 SUPs in a proper proportion, the composite HTL exhibited higher conductivity, charge carrier transfer/collection ability and greater hole injection efficiency. Additionally, the embedded SUPs also functioned as light scattering or reflecting centers to boost the light intake of the PSCs. At the optimal weight ratio of Cu_9S_5 SUPs, the average PCE of 18.21% was obtained for the $Cu_9S_5@SiO_2$ SUPs based PSC devices under one sun (AM1.5 G) illumination. Compared with PSC solar cells without $Cu_9S_5@SiO_2$ SUPs (of which the average PCE is 14.38%), a remarkable enhancement over 26% in average PCE was obtained. The basic optics and physics behind the PSC devices based on $Cu_9S_5@SiO_2$ SUPs was investigated.

2. Experimental detail

2.1. Synthesis of Cu₉S₅ NCs

The Cu₉S₅ NCs were synthesized via a typical hot injection method [36]. The copper precursor was prepared by mingling CuCl (0.01 mol) with a mixture of 4 ml of oleic acid (OA) and 5 ml of oleylamine (OM) at 130 °C for 30 min. Then the as-prepared copper precursor was cooled to room temperature. Meanwhile, the sulfur precursor was prepared by dissolving sulfur powders (0.01 mol) in 40 ml of octadecene at 200 °C for 30 min. And the sulfur solution was maintained at 180 °C, followed by swift injection of the copper precursor. Before cooling to the room temperature, the resulting solution was kept at 180 °C for 10 min Cu₉S₅ NCs in the solution were precipitated by adding excess acetone and collected by centrifugation of the suspension for two times. Finally, the precipitate was re-dispersed in an organic solvent such as cyclohexane.

2.2. Synthesis of Cu₉S₅@SiO₂ SUPs

Cu₉S₅@SiO₂ SUPs were synthesized via a modified Stöber's method [37], namely by the ammonia-catalyzed hydrolysis and condensation of tetraethylorthosilicate (TEOS) in alcohol solution. In brief, the as-prepared Cu₉S₅ NCs (0.2 g), 10 ml of cyclohexane, 0.5 ml ammonia, 10 ml Triton X-100, 8 ml hexyl alcohol, 2 ml water and 0.1 ml TEOS were successively added under stirring. After completion of TEOS addition, the mixture was allowed to react for 24 h, after which the products were collected and washed for three times with alcohol.

2.3. Device fabrication

Fluorine-doped tin oxide (FTO) coated slides (Pilkington TEC 15) were patterned by etching with Zn powders and 2 M HCl. Then, the etched slides were cleaned with liquid detergent, acetone, ethyl alcohol and de-ionized water for 15 min, sequentially, to remove the organic or inorganic residues, and finally dried in a vacuum oven. Isopropyl titanate (222 μl) and ethanol (5 ml) were blended to prepare a clear precursor sol. The precursor sol was spin-coated onto the etched FTO substrate at 4000 rpm, followed by annealing at 500 °C for 30 min to form a compact TiO₂ (c-TiO₂) film. A mesoporous TiO₂ (mp-TiO₂) film was deposited on the c-TiO₂ by spin-coating TiO₂ paste (Dyesol 18NR-T) diluted in anhydrous ethanol (weight ratio: 1:6) at 4000 rpm for 30 s. The layers were then sintered at 500 °C for 30 min in air. After cooling down to the room temperature, the samples were treated using a TiCl₄ aqueous solution at 70 °C for 30 min, and dried at 500 °C for 30 min.

A pure perovskite solution (1.25 mol l⁻¹) was made by blending CH₃NH₃I (0.2963 g) and PbI₂ (0.8678 g) powders in γ-butyrolactone (GBL) (1.05 ml) and dimethylsulfoxide (DMSO) (0.45 ml) at 60 °C for 6 h. Subsequently, the perovskite solution was then spin-coated onto the mp-TiO₂ layer by a one-step process at 4000 rpm for 50 s to form the perovskite absorber film. Anhydrous ether was dripped onto the center of the sample at 30 s during the spin-coating process.

Then, the perovskite sample was heated at 110 °C for 30 min [11, 38]. 72.3 mg of Spiro-OMeTAD, 28.8 μl of 4-tert-butyl pyridine (TBP) and 17.5 μl of Li-TFSI in acetonitrile (520 mg ml⁻¹) were dissolved in 1 ml chlorobenzene to form a Spiro-MeOTAD solution. After the perovskite film samples were cooled down to room temperature, the formed Spiro-MeOTAD solution was deposited on the perovskite layer at 4000 rpm for 30 s. To prepare Cu₉S₅@SiO₂ SUP modified HTLs, the Spiro-OMeTAD solution was mixed with the prepared chlorobenzene solution of Cu₉S₅ NCs or Cu₉S₅@SiO₂ SUPs. The used weight ratio of Cu₉S₅@SiO₂ SUPs to Spiro-OMeTAD was 0.4 wt%, 0.6 wt%, 0.8 wt%, 1 wt% and 1.2 wt%, respectively. Finally, a 100 nm thick AgAl film with an active area of 0.1 cm² was formed via evaporation on the Spiro-OMeTAD-coated film [39, 40].

2.4. Characterization of samples

The optical reflectance spectra and light absorption nature of the perovskite films were examined and characterized by a Hitachi U-3900 UV–vis spectrophotometer. The light absorption properties of the Cu₉S₅ NCs were determined via UV–vis–NIR light absorption spectroscopy (Lambda 950, PerkinElmer). The transmission electron microscope (TEM) images were recorded on a Hitachi H-800 TEM under a working voltage of 200 kV. The cross sectional view of the formed PSC device was examined by emission scanning electron microscopy (SEM) on a JEOL-2010F (JEOL Co. Ltd). X-ray diffraction (XRD) was performed using a Bruker New D8 Advance with a Cu-Kα radiation source (λ: 1.5406 A) at 40 kV and 300 mA (12 kW). The photocurrent density–voltage (*J–V*) curves were recorded via a Keithley model 2440 Source Meter under the illumination of simulated AM 1.5 G solar light from a Newport solar simulator system (equipped with a 1 kW Xenon arc lamp, Oriel, calibrated with a standard silicon reference cell). During device PV performance characterization, a metal aperture mask with an opening of about 0.09 cm² was employed. External quantum efficiency (EQE) measurements (74125, Oriel, USA) were recorded for these cells. The time-resolved PL (TRPL) spectra were collected by picosecond time-correlated single-photon counting (TCSPC) equipment. The detailed information about this picosecond TCSPC equipment is described in the [41].

3. Results and discussion

The process of fabricating Cu₉S₅@SiO₂ SUPs and the structure of Cu₉S₅@SiO₂ SUP based PSCs are displayed in Scheme 1. At the beginning, Cu₉S₅ nanospheres were grown via a hot-injection method [36]. The formed Cu₉S₅ nanospheres were mono-dispersed and homogeneous, with a diameter (*d*) of about 10 nm, as shown in figure 1(a). Cu₉S₅ nanocrystals were further inlaid in SiO₂ via the modified Stöber's approach [37], producing Cu₉S₅@SiO₂ SUPs with a diameter of about 60 nm (figures 1(b) and (c)).

The XRD patterns of the obtained Cu₉S₅ NCs and Cu₉S₅@SiO₂ SUPs match well with the standard pattern of
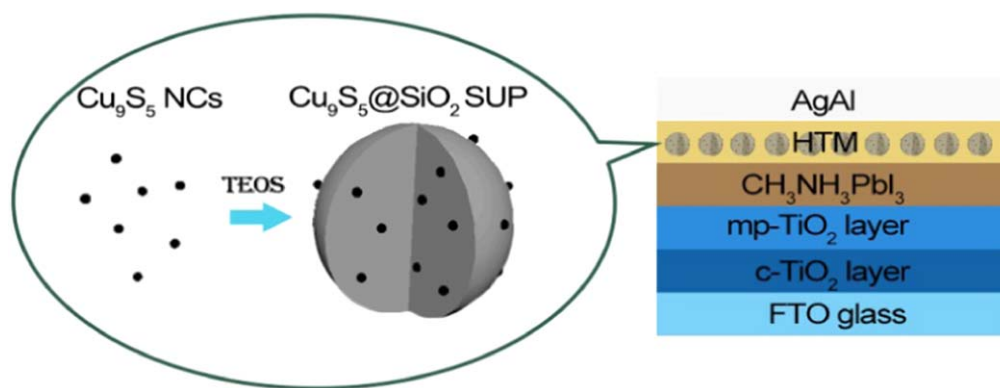
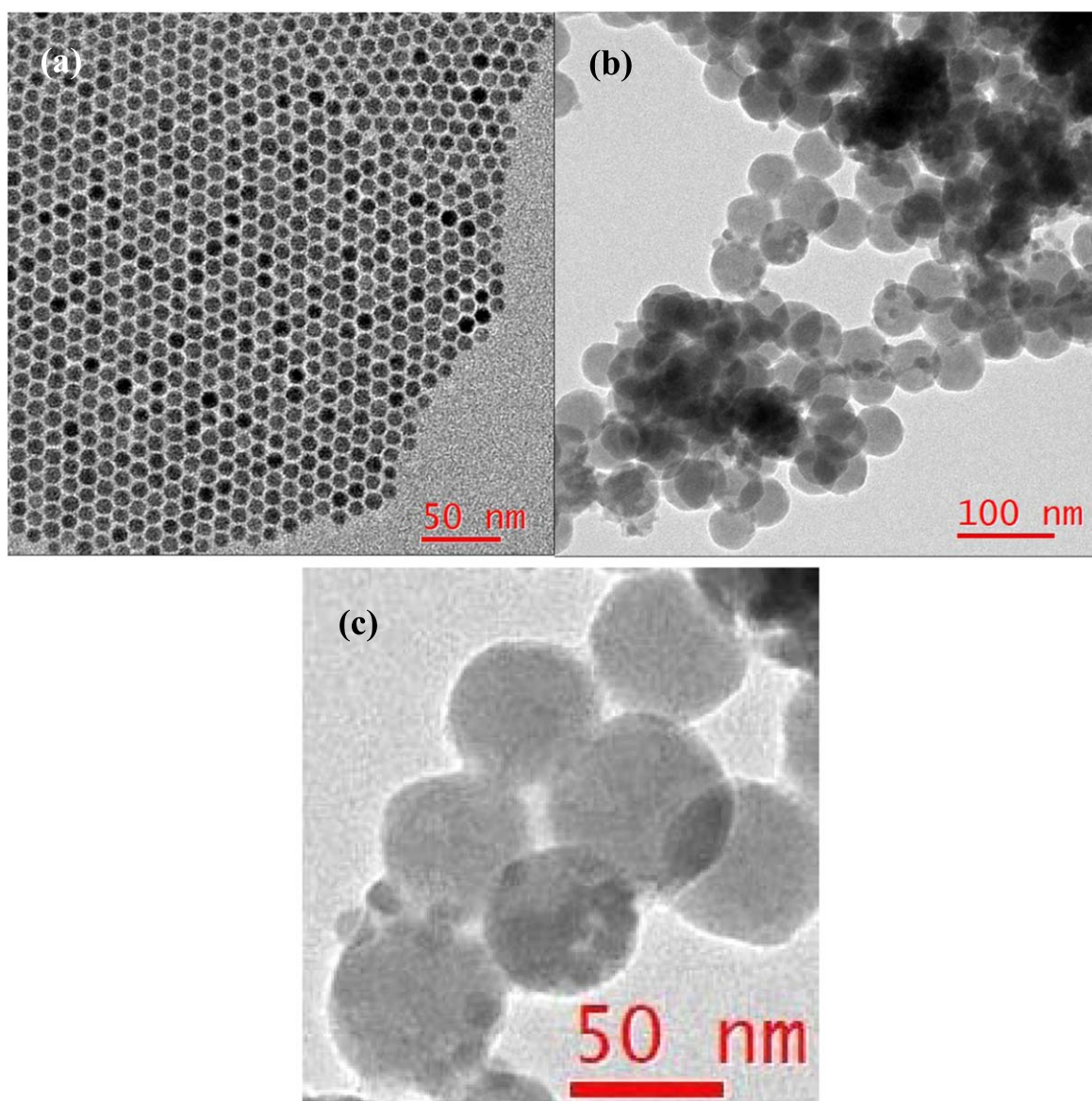**Scheme 1.** Fabrication process of $Cu_9S_5@SiO_2$ supraparticles (SUPs) and application in PSCs.

Figure 1. TEM image of (a) Cu_9S_5 nanocrystals, (b) and (c) $Cu_9S_5@SiO_2$ supraparticles.
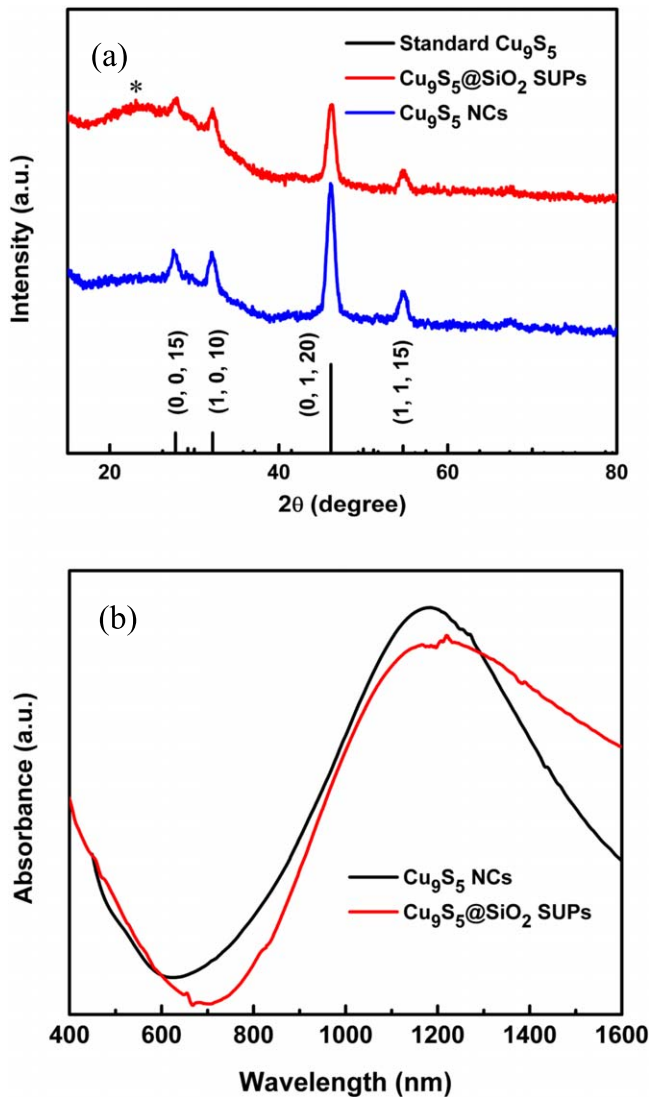
Figure 2. (a) XRD patterns of the as-prepared Cu_9S_5 NCs, $Cu_9S_5@SiO_2$ SUPs and the standard Cu_9S_5 powders on a JCPDS card (no. 47-1748). (b) UV–vis–NIR absorption spectra of Cu_9S_5 NCs and $Cu_9S_5@SiO_2$ SUPs.

Cu_9S_5 digenite phase (JCPDS no. 47-1748), as presented in figure 2(a). Several well—defined characteristic peaks corresponding to the (0, 0, 15), (1, 0, 10), (0, 1, 20) and (1, 1, 15) crystal planes specify the formation of pure rhombohedral phase of Cu_9S_5 with high crystallinity. Moreover, for the $Cu_9S_5@SiO_2$ SUP sample, the wide and weak peak centered at $2\theta = 23°$ reveals the amorphous structured silica coating within such composites [42]. The optical property of the aqueous dispersion containing Cu_9S_5 nanocrystals and $Cu_9S_5@SiO_2$ SUPs was examined by using UV–vis–NIR spectroscopy, as shown in figure 2(b). Cu_9S_5 nanocrystals clearly show a wide surface plasmon absorption band over the visible and near infrared regions centered at 1240 nm. Compared to the case of Cu_9S_5 NCs, the plasmon resonance peak of $Cu_9S_5@SiO_2$ SUPs displays an apparent redshift and a slight decrease in the intensity, caused by the silica coating [43, 44]. The localized surface plasmon resonance (LSPR) of Cu_9S_5 nanoparticles derives from collective oscillations of

excess free carriers associated with constitutional vacancies or ionized dopant impurities in the lattice, which is different from the free electron induced LSPR of metal nanostructures [45].

In order to evaluate the PV performance of the device employing $Cu_9S_5@SiO_2$ SUPs to engineer HTM films, three types of HTLs were employed, including Spiro-OMeTAD (control) without and with $Cu_9S_5@SiO_2$ SUPs or Cu_9S_5 NCs. The amount of $Cu_9S_5@SiO_2$ SUPs in Spiro-OMeTAD precursor solution was controlled as 0.4, 0.6, 0.8, 1 and 1.2 wt%, respectively, and the proportion of Cu_9S_5 NCs was 0.8 wt%. The cross-section SEM image of as-prepared PSCs is displayed in figure 3(a), from which we can confirm the layered structure of the PSC device. The photocurrent density–voltage curves (*J–V*) of the PSCs measured under one sun illumination at AM 1.5 G are shown in figure 3(b). The corresponding average PV parameters and the dependence on $Cu_9S_5@SiO_2$ SUP or Cu_9S_5 NC concentrations have been determined and the results are summarized in table 1. As can be seen from figure 3(a) and table 1, the control device without modification reveals an average short-circuit current density (J_{SC}) 21.24 mA cm^{-2}, a mean open-circuit voltage (V_{OC}) 1.01 V, an average fill factor (FF) of 67.06% and PCE of 14.38%. The corresponding cells based on a low content of 0.4 wt% $Cu_{2-x}S@SiO_2$ SUPs induced a higher V_{OC} and J_{SC}, resulting in a slightly enhanced average PCE of 14.78%. Employing $Cu_9S_5@SiO_2$ SUPs as additive to HTLs, a simultaneous enhancement in V_{OC}, J_{SC} and FF can be observed as the amount of $Cu_9S_5@SiO_2$ SUPs is increased from 0.4 wt% to 0.8 wt%. Specifically, the V_{OC} increases from 1.01 to 1.05 V, the J_{SC} increases from 22.24 to 23.14 mA cm^{-2}, and most distinctly the FF increases from 65.16% to over 74.95%. As a consequence, the devices obtained from the Spiro-OMeTAD solution with 0.8 wt% $Cu_9S_5@SiO_2$ SUPs provided average efficiencies of 18.21%. In solar cells, the FF was reported to principally be associated with the series resistance (R_S) and shunt resistance (R_{SH}) [46, 47], which can be estimated from the *J–V* results. The increased FF is in well coincident with the decreased R_S and increased R_{SH} which can be seen from table 1. The lowest R_S and highest R_{SH} is in well coincident with the largest FF for the PSC based on 0.8 wt% $Cu_9S_5@SiO_2$ SUPs. However, a further increase in the amount of $Cu_9S_5@SiO_2$ SUPs from 0.8 wt% to 1.0 wt%, or even 1.2 wt% leads to a dramatically reduced V_{OC}, FF and PCE. Besides, Cu_9S_5 nanocrystals were also incorporate into HTLs. The PV performance of the PSC devices without modification and with 0.8 wt% Cu_9S_5 NCs or 0.8 wt% $Cu_9S_5@SiO_2$ SUPs was more clearly compared and shown in figure 3(c). As can be seen from table 1, the device based on 0.8 wt% Cu_9S_5 NCs exhibits an average J_{SC} of 22.43 mA cm^{-2}, V_{OC} of 1.05 V, FF of 72.40% and PCE of 17.05%. These PV parameter values are higher than those of the control, nevertheless, obviously lower than those of the PSC bases on $Cu_9S_5@SiO_2$ SUPs. The approach by incorporating $Cu_9S_5@SiO_2$ SUPs into HTLs at the optimal weight ratio of 0.8 wt% significantly boosts the average PCE to 18.21%. Figure 3(d) shows the EQE spectra of the PSC devices without modification and with 0.8 wt% Cu_9S_5 NCs or
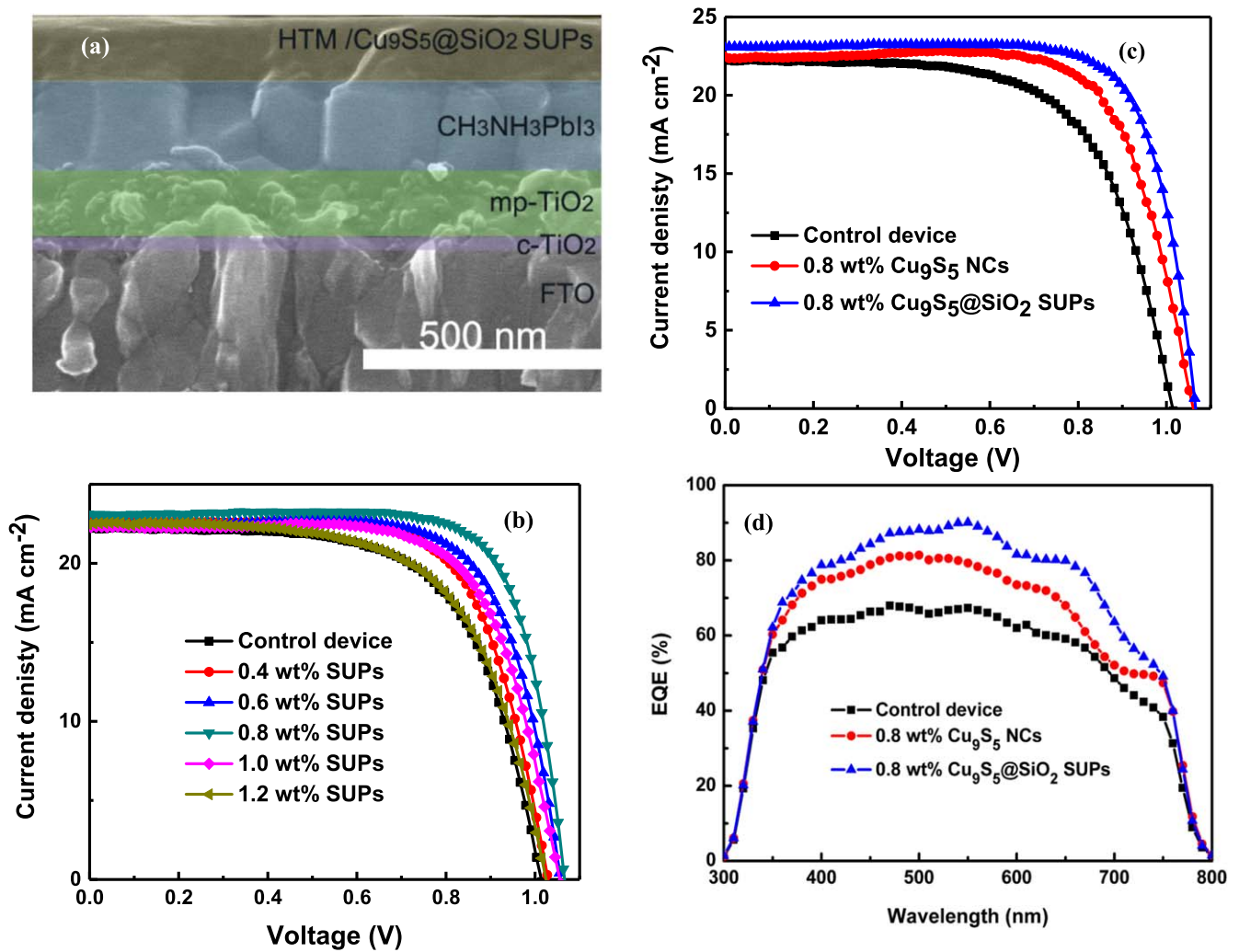
Figure 3. (a) Cross-sectional SEM image of $Cu_9S_5@SiO_2$ supraparticle based PSCs. (b) *J–V* characteristics of PSC devices with different amounts of $Cu_9S_5@SiO_2$ supraparticles. (c) *J–V* characteristics and (d) EQE spectra of the control device, and PSCs with 0.8 wt% Cu_9S_5 NCs or 0.8 wt% $Cu_9S_5@SiO_2$ supraparticles.

Table 1. Photovoltaic parameters of PSCs using hybrid HTLs with various ratios of $Cu_9S_5@SiO_2$ supraparticles or Cu_9S_5 nanocrystals.

Sample (wt%)	V_{OC} (V)	J_{SC} (mA cm^{-2})	FF (%)	PCE (%)	R_S (Ω cm^2)	R_{SH} (Ω cm^2)
Control device	1.01 ± 0.01	21.24 ± 1.02	67.06 ± 3.06	14.38 ± 0.16	81	42 503
0.4 wt% SUPs	1.02 ± 0.02	21.96 ± 0.71	69.58 ± 0.61	15.66 ± 0.52	82	59 906
0.6 wt% SUPs	1.02 ± 0.02	22.50 ± 0.35	70.23 ± 1.62	16.12 ± 0.84	57	70 377
0.8 wt% SUPs	1.05 ± 0.02	23.14 ± 0.10	74.95 ± 0.72	18.21 ± 0.61	44	136 448
1.0 wt% SUPs	1.02 ± 0.01	22.67 ± 0.09	70.62 ± 1.07	16.42 ± 0.23	71	102 485
1.2 wt% SUPs	1.01 ± 0.01	22.11 ± 0.40	64.49 ± 0.67	14.49 ± 0.13	101	47 519
0.8 wt% Cu_9S_5 NCs	1.05 ± 0.01	22.43 ± 0.41	72.40 ± 1.46	17.06 ± 0.34	55	80 446

0.8 wt% $Cu_9S_5@SiO_2$ SUPs as a function of the wavelength. The generation of photocurrent starts at ∼800 nm for all three devices. Thus, the spectral response of the PSCs are limited to the wavelength range of 300–800 nm, which is far away from to the absorption peak of Cu_9S_5 nanomaterials shown in figure 2(b), implying that the solar light harvesting enhancement induced by LSPRs of Cu_9S_5 nanostructures is finite in $CH_3NH_3PbI_3$ based PSCs. From figure 3(d), within the wavelength range from 400 to 750 nm, the photocurrent

increased remarkably after incorporating Cu_9S_5 NCs and $Cu_9S_5@SiO_2$ SUPs compared to the control device, especially for the case of $Cu_9S_5@SiO_2$ SUPs, which is in good agreement with the J_{SC} extracted from the corresponding *J–V* curve shown in figure 3(c). Moreover, the EQE spectrum of the PSC device based on 0.8 wt% $Cu_9S_5@SiO_2$ SUPs exhibits significantly higher quantum yields over a wide wavelength scope from 350 to 750 nm with a maximal value of 91%. When employing Cu_9S_5 NCs or $Cu_9S_5@SiO_2$ SUPs as
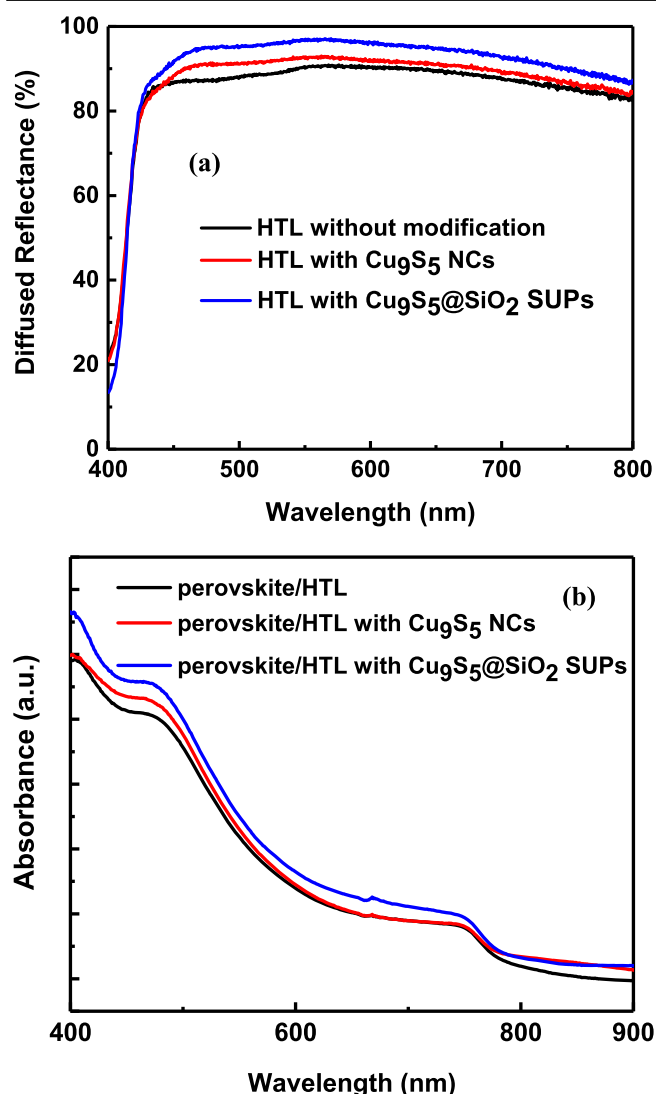
Figure 4. (a) Diffused reflectance spectra of glass/FTO/ bare HTL/ AgAl and glass/FTO/ HTL@0.8 wt% Cu_9S_5 NCs or Cu_9S_5@SiO_2 SUPs/AgAl samples. (b) UV–vis absorption spectra of glass/ $CH_3NH_3PbI_3$/bare HTL and glass/$CH_3NH_3PbI_3$/HTL@0.8 wt% Cu_9S_5 NCs or Cu_9S_5@SiO_2 SUPs samples.

additive to HTLs, the increase in V_{OC}, J_{SC}, FF or EQE values may be ascribed to the improved scattering and electronic properties of HTLs by addition of these Cu_9S_5 based nanomaterials. The corresponding discussion will be made in the subsequent sections.

To understand the underlying optical mechanism of the PV performance enhancement in the Cu_9S_5@SiO_2 SUPs incorporated PSC device, the optical natures of HTL/AgAl and perovskite/HTL hybrid layers, the important component parts for PSC devices, were probed. Figure 4(a) displays the diffused reflectance spectra of glass/FTO/bare HTL/AgAl and glass/FTO/HTL containing 0.8 wt% Cu_9S_5

NCs or Cu_9S_5@SiO_2 SUPs/AgAl samples. The light scattering (reflection) of the composite HTL-back metal electrode sample slightly but clearly increases by the addition of Cu_9S_5 NCs, and considerably increases by the incorporation of Cu_9S_5@SiO_2 SUPs in the optical region from

450 to 800 nm. These results undoubtedly suggest that the Cu_9S_5 NCs or Cu_9S_5@SiO_2 SUPs act as scattering centers and increase the light path inside the PSC device. The tremendously strengthened reflectance in the Cu_9S_5@SiO_2 SUP modified HTL/AgAl sample definitely confirm the more effective light scattering or reflecting of Cu_9S_5@SiO_2 SUPs than Cu_9S_5 NCs both in the visible and NIR regime. The more effective light scattering or reflecting of Cu_9S_5@SiO_2 SUPs could extend both visible and NIR light path-lengths within the perovskite active layer and thus efficiently boost solar light harvesting in the PSC device. Figure 4(b) displays the UV–vis absorption spectra of hybrid samples consisted of glass/$CH_3NH_3PbI_3$/HTL without modification and with Cu_9S_5 NCs or Cu_9S_5@SiO_2 SUPs modification. The sample of glass/$CH_3NH_3PbI_3$/HTL containing Cu_9S_5 NCs or Cu_9S_5@SiO_2 SUPs shows more intense absorption over 400–900 nm than the control sample without modification, due to the scattering or reflecting effect of Cu_9S_5 NCs and SUPs. It is noted that the absorbance of the perovskite composite sample is most dramatically enhanced over 400–900 nm with the addition of Cu_9S_5@SiO_2 SUPs, as expected from the reflectance results shown in figure 4(a). The absorption results for perovskite composite samples based on differently structured HTLs are in good agreement with those from *J–V* and EQE measurements shown in figures 3(c) and (d). When sunlight is incident on the PSC, the light transmitting through the glass and the FTO layer was absorbed by the perovskite layer. The unabsorbed light energy, especially for long-wavelength light, was reflected back into the perovskite absorber by the Cu_9S_5 NCs, the Cu_9S_5@SiO_2 SUPs or the back AgAl electrode and absorbed again by the perovskite to generate extra charge carriers, leading to an enhancement in the performance of the PSCs shown in table 1 and figure 3. Therefore, the intense efficiency enhancement in the PSC device by addition of Cu_9S_5@SiO_2 SUPs can be at least partially associated with the relatively effectively scattering or reflecting effect of Cu_9S_5@SiO_2 SUPs.

On the other hand, using the EQE and absorption measurement data shown in figures 3(d) and 4(b), we further calculate the increase percentage in EQE ($\Delta EQE/EQE_{ref}$) and absorption ($\Delta Abs/Abs_{ref}$) with the addition of Cu_9S_5 NCs or Cu_9S_5@SiO_2 SUPs, which we show in figure S1 (available online in the supplementary information stacks.iop. org/NANO/30/445401/mmedia). From the figure, the EQE enhancement is broadly distributed over the wide range from 350 to 750 nm with a maximal value at 650 nm for the PSC based on Cu_9S_5@SiO_2 SUPs and does not specifically follow the plasmon mode profile shown in figure 2(b). Moreover, for the case modified with Cu_9S_5 NCs or Cu_9S_5@SiO_2 SUPs, the enhancement percentage obtained from the light absorption of the perovskite composite sample is much lower than that of the EQE incremental quantity over the wavelength range of 400–650 nm, where the spectral response of the solar cell is high. When the wavelength is near and beyond the edge of the absorption band of perovskite film, the sharply increased absorption enhancement could be attributed to the quick increase absorption of the Cu_9S_5 nanomaterials. The broad
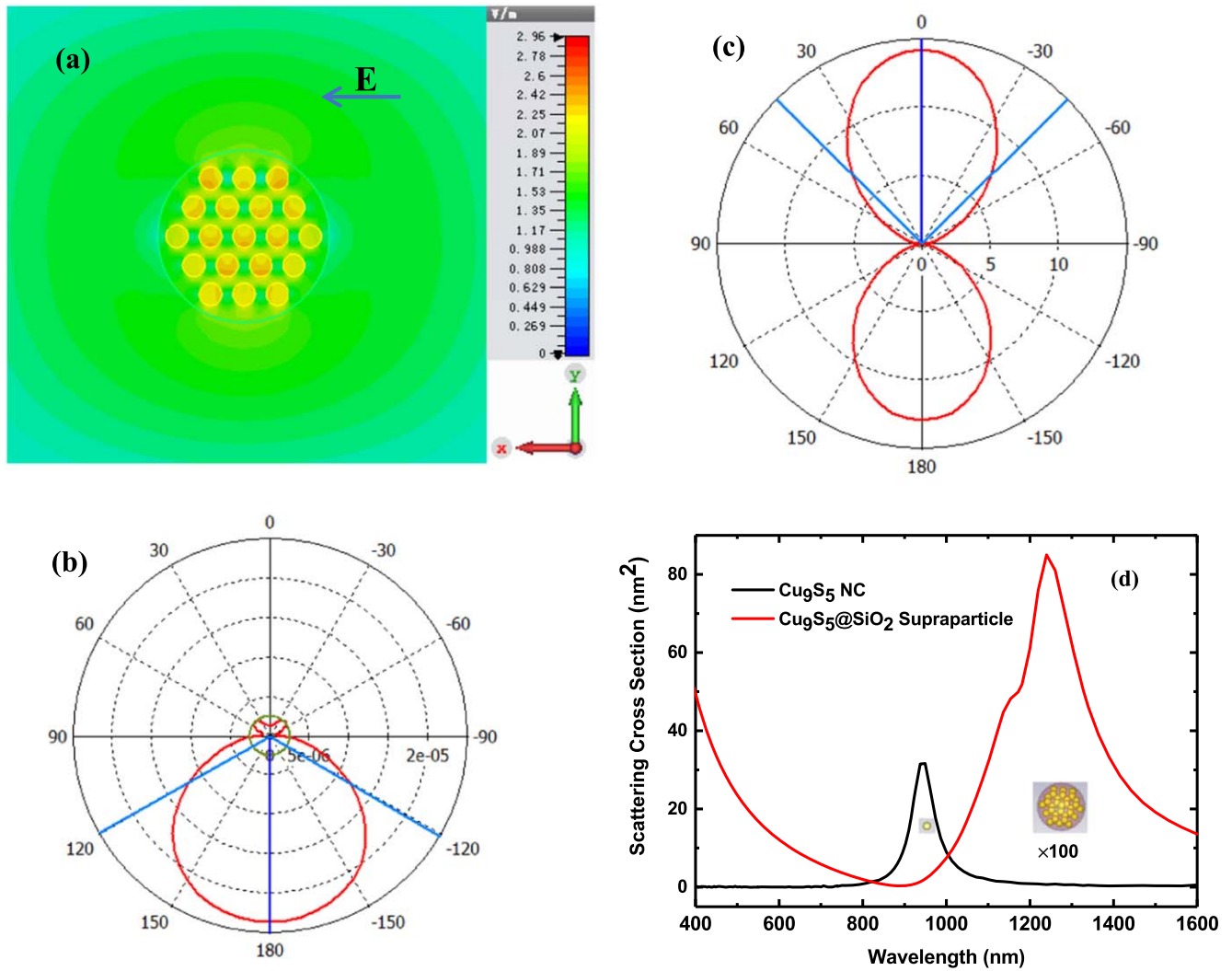
Figure 5. (a) Simulated field $|E|$ enhancement distribution of 60 nm $Cu_9S_5@SiO_2$ supraparticle in the HTM. Scattering diagrams for a (b) 10 nm Cu_9S_5 nanosphere and a (c) 60 nm $Cu_9S_5@SiO_2$ supraparticle illuminated by a linear polarized plane wave in free space. (d) Calculated scattering cross sections of 10 nm Cu_9S_5 nanocrystal and 60 nm $Cu_9S_5@SiO_2$ supraparticle.

and intense EQE enhancement in the high spectral response range of the device suggests that the enhanced device performance of Cu_9S_5 NC or SUP composite PSCs mainly come from semiconductor plasmonically enhanced electrical properties of the Cu_9S_5 composite HTL, rather than from optical effects alone [7, 8, 31].

Light incident on semiconductor nanoparticles can be scattered into the far-field, depending on geometric and material properties of the particle [48, 49]. Finite-difference time-domain (FDTD) numerical simulations were performed for spherical Cu_9S_5 NC and $Cu_9S_5@SiO_2$ SUP. The computation was based on the finite integral technique (CST Microwave Studio) [7, 8, 49]. The optical properties (refractive index, n, and extinction coefficient, k) of the related materials are from the data in previous publications [36, 50–52]. FDTD numerical simulations were performed for a $Cu_9S_5@SiO_2$ spherical SUP embedded in HTM. The center of the $Cu_9S_5@SiO_2$ SUP located at the origin. Figure 5(a) shows the calculated local amplitude enhancement distribution of the electric field $|E|$ in the xy plane for an incident light

at $\lambda = 550$ nm, where the maximal absolute EQE value was obtained. From figure 5(a), the electric field is enhanced and localized inside or around the Cu_9S_5 crystals or $Cu_9S_5@SiO_2$ SUP, and the maximum $|E|$ enhancement factor is about 2.4. The near field enhancement can be a result of coupling between individual plasmonic Cu_9S_5 particles and the interaction between $Cu_9S_5@SiO_2$ SUPs and HTM in close proximity [53]. When semiconductor NPs in a SUP are very adjacent to each other, higher-order interactions and even energy transfer may occur.

Figure 5(b) and (c) show angular scattering diagrams for a 10 nm Cu_9S_5 nanoparticle and 60 nm $Cu_9S_5@SiO_2$ SUP illuminated by a linear polarized plane wave with a wavelength (λ) of 550 nm in free space. An angle of 0° correlates with backward scattering while 180° correlates with forward scattering. The Cu_9S_5 nanoparticles scatter more radiation in the forward direction than in the backward direction (figure 5(b)). In contrast, for the $Cu_9S_5@SiO_2$ spherical SUP, the far-field angular distribution pattern becomes more backscattering (figure 5(c)). These results are consistent with prior

research [31, 54]. In the case of spherical nanoparticles, relatively smaller particles are known to result in more scattering in the forward direction while larger particles scatter more in the backward direction (as a reflection).

Figure 5(d) shows the calculated scattering cross-sections of spherical Cu_9S_5 nanoparticle and $Cu_9S_5@SiO_2$ SUP in free space. Multiple Cu_9S_5 nanoparticles with a small size were assemble into a nanocapsule with a large size using silica to form a $Cu_9S_5@SiO_2$ SUP. The scattering efficiency of $Cu_9S_5@SiO_2$ SUP peaks at 1240 nm due to the surface plasmon resonance of multiplex Cu_9S_5 NPs, as shown in figure 2(b). Moreover, the $Cu_9S_5@SiO_2$ SUP has tremendously stronger scattering properties than the Cu_9S_5 nanoparticle. The scattering cross section of the former is two orders of magnitude larger than that of the latter. This result strongly support the much more effectively scattering or reflecting effect of $Cu_9S_5@SiO_2$ SUPs blended in HTL/AgAl of the PSC device. This far-field scattered light can ultimately be reabsorbed by the perovskite semiconductor, enabling enhanced light absorption, photocurrent and thus, PCE in $Cu_9S_5@SiO_2$ SUPs based PSCs.

Cu_9S_5 is a good hole-conducting inorganic material, which can be applied as the back electrode for CdTe solar cells [27]. For a $Cu_9S_5@SiO_2$ SUP, multiple Cu_9S_5 NCs are in close proximity to each other, and encapsulated by SiO_2. At the same time, some Cu_9S_5 NCs are left exposed on the surface of the SUP, as shown in figure 1(c). $Cu_9S_5@SiO_2$ SUPs allow the combination of multiple Cu_9S_5 NCs into a single entity. Such SUPs not only carry on the good electrical conductivity and hole-transport capacity of its constituent building blocks, i.e. Cu_9S_5 NCs, but may reveal additional functional properties, hence surpassing the sum of its parts. Higher-order interactions and even tunneling may take place between the Cu_9S_5 NCs in the SUPs [50]. Therefore, in addition to the function as scattering or reflecting center to increase the total light energy trapped within the PSCs, doping of $Cu_9S_5@SiO_2$ SUPs can also improve the electrical conductivity and hole-transport capacity of HTL. In order to carry out the related tests, the precursor HTM solutions without modification and modified with 0.8 wt% Cu_9S_5 NCs or $Cu_9S_5@SiO_2$ SUPs were directly deposited on FTO slides to prepare HTLs, and subsequently, 100 nm thick AgAl film was evaporated on the grown HTLs. The structure of the multi-layered device is exhibited in the inset of figure S3. *J–V* characteristics of the multi-layered device were measured by applying a bias between the AgAl electrodes on the HTM and the FTO layers and under dark conditions, as shown in figure S3. The conductivity of the spiro-MeOTAD based HTL with and without modification can be simulated from *J–V* characteristics of this two-contact electrical conductivity set-up [18]. The value we obtain for the conductivity in pure spiro-MeOTAD is 1.74×10^{-6} S cm^{-1}, in very good agreement with that reported in [55]. The conductivity increases with the addition of 0.8 wt% Cu_9S_5 NCs or $Cu_9S_5@SiO_2$ SUPs, exhibiting 3.64×10^{-6} Scm^{-1} and 4.09×10^{-6} S cm^{-1}, respectively. Encouragingly, when the small amount of $Cu_9S_5@SiO_2$ SUPs is added, the conductivity increases by 2.3 times. The result substantiates that the introduction of the $Cu_9S_5@SiO_2$

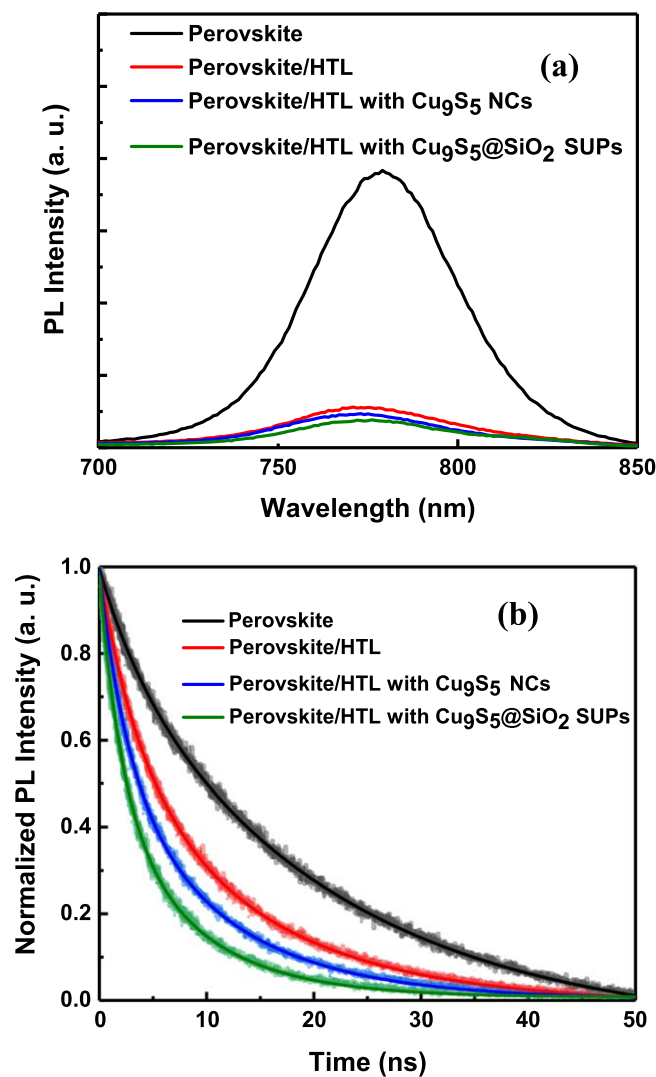**Figure 6.** Steady-state PL spectra (a) and time-resolved PL decays (b) of samples consisting of glass/$CH_3NH_3PbI_3$ and glass/$CH_3NH_3PbI_3$/HTL without modification and with 0.8 wt% Cu_9S_5 NCs and 0.8 wt% $Cu_9S_5@SiO_2$ SUPs.

SUPs remarkably enhances the conductivity of HTL and is well-matched with the improved performance of PSCs mentioned in the previous sections.

To investigate the charge transfer process at the perovskite and Cu_9S_5 NCs, $Cu_9S_5@SiO_2$ SUPs modified HTL interface, steady-state photoluminescence (PL) and TRPL decay transient spectra were recorded for the $CH_3NH_3PbI_3$/HTL samples prepared on glass substrates. As can be seen from figure 6(a), the bare perovskite film shows a strong emission peak at about 760 nm, and the PL is significantly quenched when the bare Spiro-OMeTAD HTL is applied onto the perovskite film, indicating that efficient charge carrier transfer at the perovskite/HTL interface. When the Cu_9S_5 NCs and $Cu_9S_5@SiO_2$ SUPs incorporated HTL is used, the PL quenching is even more intensely, especially for the case of the $Cu_9S_5@SiO_2$ SUPs modified HTL. Quenching effects clearly indicated that the introduction of $Cu_9S_5@SiO_2$ SUP into the HTL facilitated charge transfer and separation at the perovskite/HTL interface. The $CH_3NH_3PbI_3$/HTL

Table 2. Summarized fitting parameters taken from the time-resolved PL curves in figure 6(b) by two exponential decay functions and average PL decay lifetimes (τ_{av}), PL rate constants (k_{PL}), injection rate constants (k_{inj}), and injection efficiencies (Φ_{inj}) of different samples.

Sample	A_1	τ_1 (ns)	A_2	τ_2 (ns)	τ_{av} (ns)	k_{PL} (s^{-1})	k_{inj} (s^{-1})	Φ_{inj} (%)
Perovskite	12.43%	3.93	87.57%	21.26	20.81	4.8×10^7	—	—
Perovskite/HTL	38.19%	3.76	61.81%	13.74	12.29	8.1×10^7	3.3×10^7	40.74
Perovskite/HTL @Cu$_9$S$_5$ NCs	44.66%	2.71	55.34%	10.74	9.38	1.1×10^8	6.2×10^7	56.36
Perovskite/HTL @Cu$_9$S$_5$ SUPs	48.89%	2.11	51.11%	8.04	6.85	1.5×10^8	1.0×10^8	66.67

containing Cu$_9$S$_5$@SiO$_2$ SUPs sample exhibits the lowest PL peak intensity and the strongest degree of PL quenching. The most intense PL quenching suggests the rapidest charge transfer, the most effective hole extraction and the lowest recombination rate, and hence likely the highest short-circuit current, FF and the best PV performance [55, 56]. These results are further supported by the TRPL measurements shown in figure 6(b). The PL lifetimes of these bilayer samples were characterized by monitoring the peak emission at 760 nm. The TRPL spectra can provide an insight into the photo-physical properties of PSCs, including the charge accumulation at perovskite/HTL interface and the charge transfer or charge separation/injection behavior [57, 58]. The PL decay spectra can be well-fitted using a two-exponential equation, yielding a fast decay characterized by the lifetime, τ_1, together with a slow component, τ_2. It is known that the fast decay process reflects the charge carrier capturing by defects and the radiative decay process, and the slow decay process is mainly associated with the charge carrier transfer process across the interface [59]. Therefore, in this paper, slow decay times are utilized to comparison. The pristine perovskite film displays the largest PL lifetime with τ_2 of 21.26 ns. The PL lifetime is significantly shortened when Spiro-OMeTAD layer is coated onto perovskite film. The corresponding τ_2 value for the case of the bare HTL is 13.74 ns. When the Cu$_9$S$_5$ NCs are doped into HTL, the formed perovskite/HTL with Cu$_9$S$_5$ NCs displays faster decay with a τ_2 of 10.74 ns. It can be noticed that when the HTL is doped with Cu$_9$S$_5$@SiO$_2$ SUPs, the device exhibits the fastest decay with a τ_2 of 8.04 ns. This can be attributed to the efficient charge carrier transfer and high hole mobility induced by the incorporation of Cu$_9$S$_5$@SiO$_2$ SUPs. Both the steady-state and TRPL decay results matched well. There is no doubt that the Cu$_9$S$_5$@SiO$_2$ SUPs based PSCs exhibited the highest J_{SC}, V_{OC}, and FF values for all of the devices tested here, clearly suggesting the better hole-collection ability with the addition of Cu$_9$S$_5$@SiO$_2$ SUPs into Spiro-OMeTAD. The results show a definite effect of p-doping in improving the charge carrier transport/extraction of the HTL.

The average PL decay time (τ_{av}) was calculated by the following equation (1): [60]

$$\tau_{av} = \frac{\sum A_i \tau_i^2}{\sum A_i \tau_i}.$$ (1)

The value of τ_{av} of different device was shown in table 2. The hole injection efficiency, Φ_{inj}, can be expressed by

equation (2):

$$\Phi_{inj} = k_{inj}/(k_{inj} + k_o).$$ (2)

Here the injection constant (k_{inj}) is defined as $k_{inj} = k_{HTL} - k_o$, where k_{HTL} and k_o is the PL rate constant determined from the PL lifetimes of the perovskite film with different types of HTL and single perovskite film, respectively. In general, these rate constants can be expressed by the inverse of the monitored emission lifetimes, τ_{av}, which was determined by TRPL measurement [61, 62]. The specific data is shown in the table 2. For the unmodified HTL sample, the hole injection efficiency is 40.74%. When Cu$_9$S$_5$ NCs are incorporated into HTL, the hole injection efficiency increases to 56.36%. When Cu$_9$S$_5$@SiO$_2$ SUPs are added into HTL, the hole efficiency increases up to 66.67%. This result further demonstrates the addition of Cu$_9$S$_5$@SiO$_2$ SUPs leads to significant enhanced hole injection from perovskite film to HTL.

4. Conclusions

We have developed efficient PSCs by embedding Cu$_9$S$_5$@SiO$_2$ SUPs into Spiro-OMeTAD based HTLs. High quality and mono-disperse Cu$_9$S$_5$ NCs were synthesized using a hot-injection approach. Cu$_9$S$_5$@SiO$_2$ SUPs were form by embedding numerous Cu$_9$S$_5$ NCs in silica. Cu$_9$S$_5$@SiO$_2$ SUPs were added into Spiro-OMeTAD based HTLs with different weight ratios. The contribution of the optical and electrical effects of Cu$_9$S$_5$@SiO$_2$ SUPs to the PV performance improvement has been investigated through theoretical modeling and experiment. Both theoretical and experimental studies show that the intense light scattering or reflecting natures of Cu$_9$S$_5$@SiO$_2$ SUPs embedded in the PSC device in a suitable proportion donates to boost the light energy trapped within the device, resulting in clearly enhanced light absorption in the active layer. In addition, the incorporated Cu$_9$S$_5$@SiO$_2$ SUPs remarkably improve the electrical conductivity and hole-transport characteristics of the HTL. With using Cu$_9$S$_5$@SiO$_2$ SUPs at the optimal ratio, the conductivity and the hole injection efficiency in the HTM were 2.3 and 1.6 times higher than those of the pure Spiro-OMeTAD HTL without modification. Consequently, the incorporation of an optimized ratio Cu$_9$S$_5$@SiO$_2$ SUPs in PSC devices promotes the average PCE from 14.38% to 18.21%, displaying over 26% enhancement compared with the reference device without Cu$_9$S$_5$ modification. Our research provides an innovative approach to enormously improve the PV

performance of heterojunction PSC devices by applying optically scattering p-type semiconductor SUPs.

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